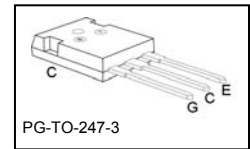
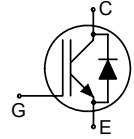


Low Loss DuoPack : IGBT in TrenchStop® and Fieldstop technology with anti-parallel diode

**Features:**

- 1.1V Forward voltage of antiparallel rectifier diode
- Specified for  $T_{jmax} = 175^{\circ}\text{C}$
- TrenchStop® and Fieldstop technology for 1000 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - easy parallel switching capability due to positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Qualified according to JEDEC<sup>1</sup> for target applications
- Application specific optimisation of inverse diode
- Pb-free lead plating; RoHS compliant



**Applications:**

- Microwave Oven
- Soft Switching Applications

Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^{\circ}\text{C}}$	$T_{j,max}$	Marking	Package
IHW30N100T	1000V	30A	1.55V	175°C	H30T100	PG-TO-247-3

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1000	V
DC collector current	$I_C$	60 30	A
$T_C = 25^{\circ}\text{C}$			
$T_C = 100^{\circ}\text{C}$			
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	90	
Turn off safe operating area $V_{CE} \leq 1000\text{V}$ , $T_j \leq 175^{\circ}\text{C}$	-	90	
Diode forward current	$I_F$	22 12	
$T_C = 25^{\circ}\text{C}$			
$T_C = 100^{\circ}\text{C}$			
Diode pulsed current, $t_p$ limited by $T_{jmax}$	$I_{Fpuls}$	36	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Transient Gate-emitter voltage ( $t_p < 5$ ms)		$\pm 25$	
Power dissipation, $T_C = 25^{\circ}\text{C}$	$P_{tot}$	412	W
Operating junction temperature	$T_j$	-40...+175	°C
Storage temperature	$T_{stg}$	-55...+175	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JESD-022

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.36	K/W
Diode thermal resistance, junction – case	$R_{thJCD}$		1.1	
Thermal resistance, junction – ambient	$R_{thJA}$		40	

### Electrical Characteristic, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	1000	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=30A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ $T_j=175^\circ\text{C}$	1.3 - -	1.55 1.7 1.8	1.7 - -	
Diode forward voltage	$V_F$	$V_{GE}=0V, I_F=10A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ $T_j=175^\circ\text{C}$	- - -	1.1 1.0 1.0	1.3 - -	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=700\mu A, V_{CE}=V_{GE}$	5.1	5.8	6.4	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1000V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	- -	- -	5 2500	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	600	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=30A$	-	28	-	S

### Dynamic Characteristic

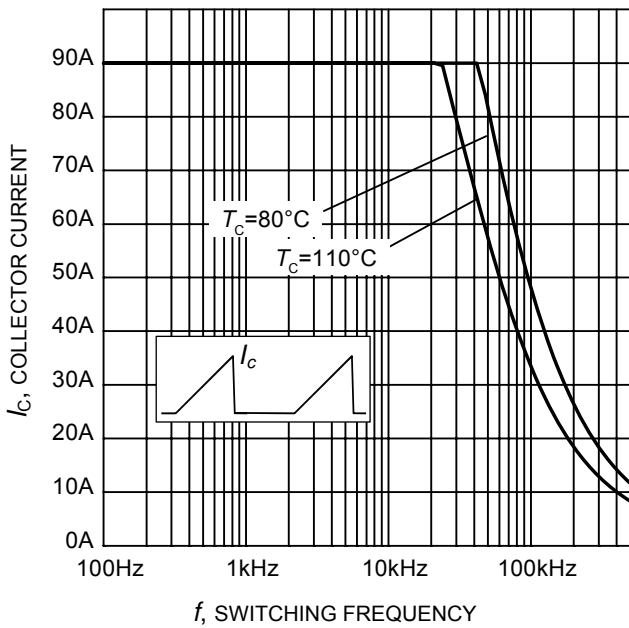
Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	3573	-	pF
Output capacitance	$C_{oss}$		-	98	-	
Reverse transfer capacitance	$C_{rss}$		-	76	-	
Gate charge	$Q_{Gate}$	$V_{CC}=800V, I_C=30A$ $V_{GE}=15V$	-	217	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13	-	nH

### Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

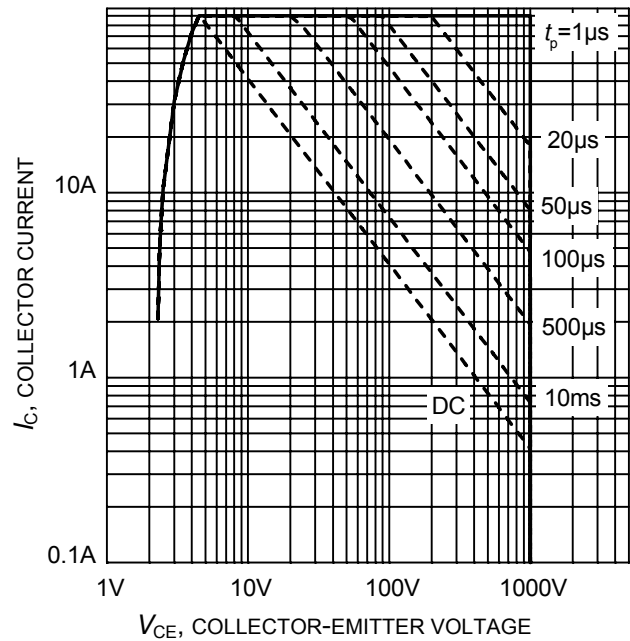
Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$ , $V_{CC}=600\text{V}$ , $I_C=30\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=15\Omega$ ,	-	35	-	ns
Rise time	$t_r$		-	22	-	
Turn-off delay time	$t_{d(off)}$		-	546	-	
Fall time	$t_f$		-	27	42	
Turn-on energy	$E_{on}$	Energy losses include "tail" and diode reverse recovery.	-	-	-	mJ
Turn-off energy	$E_{off}$		-	1.6	2.6	
Total switching energy	$E_{ts}$		-	-	-	

### Switching Characteristic, Inductive Load, at $T_j=175^\circ\text{C}$

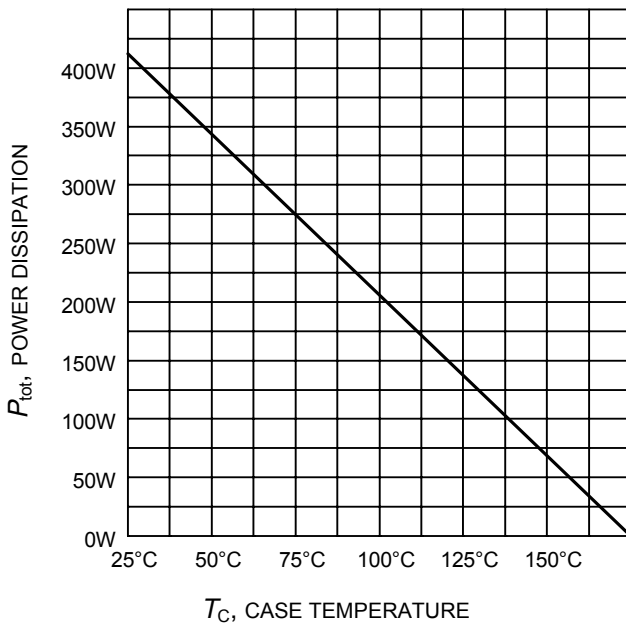
Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=175^\circ\text{C}$ $V_{CC}=600\text{V}$ , $I_C=30\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=15\Omega$ ,	-	33	-	ns
Rise time	$t_r$		-	36	-	
Turn-off delay time	$t_{d(off)}$		-	623	-	
Fall time	$t_f$		-	37	70	
Turn-on energy	$E_{on}$	Energy losses include "tail" and diode reverse recovery.	-	-	-	mJ
Turn-off energy	$E_{off}$		-	2.3	4	
Total switching energy	$E_{ts}$		-	-	-	



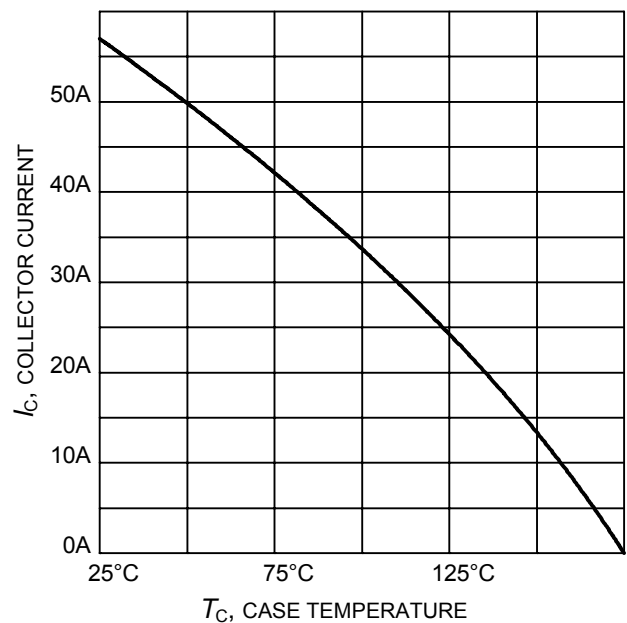
**Figure 1. Collector current as a function of switching frequency for triangular current ( $E_{on} = 0$ , hard turn-off)**  
 ( $T_j \leq 175^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $R_G = 26.9\Omega$ )



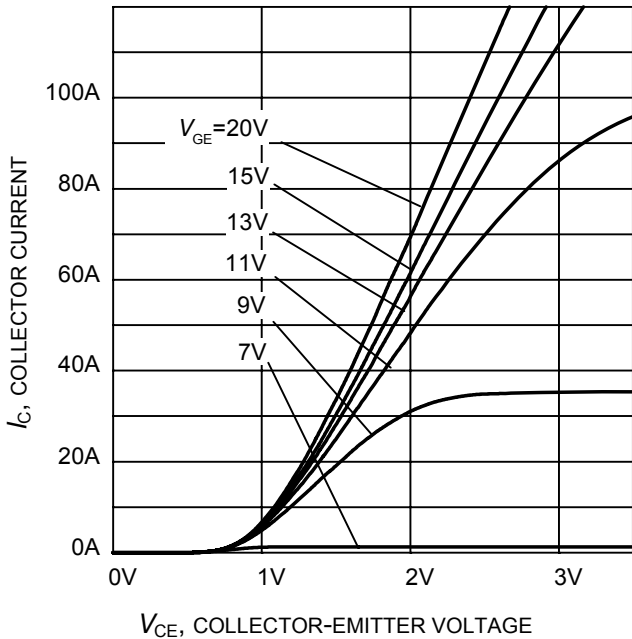
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 175^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$ )



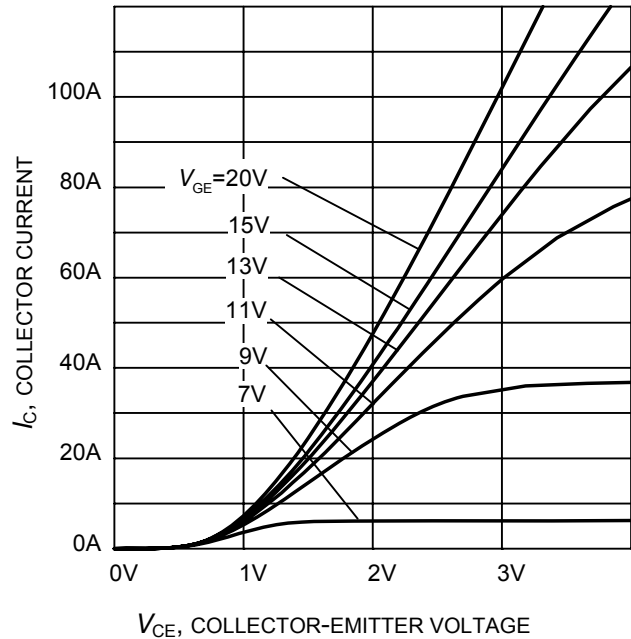
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 175^\circ\text{C}$ )



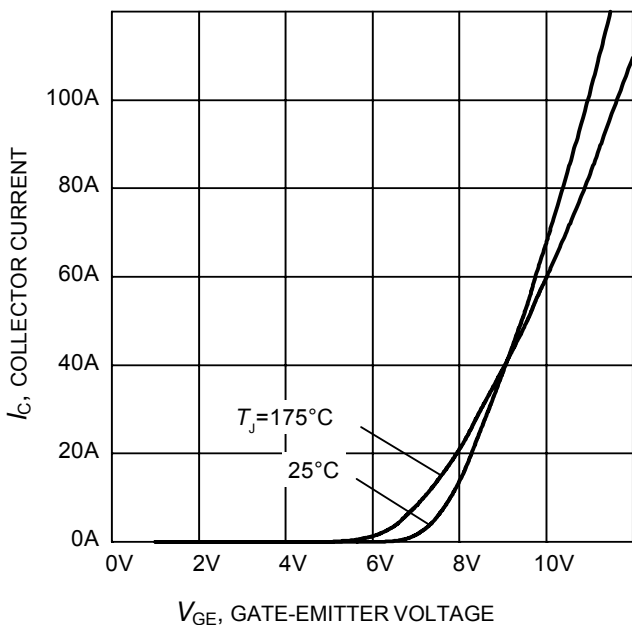
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 175^\circ\text{C}$ )



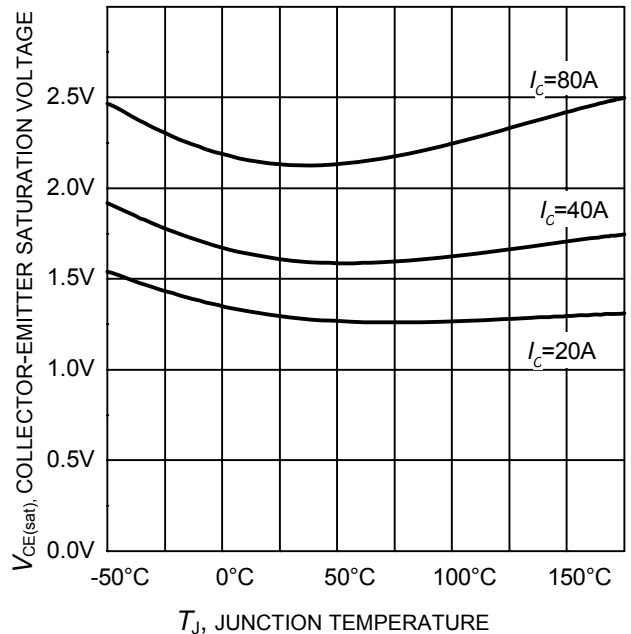
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



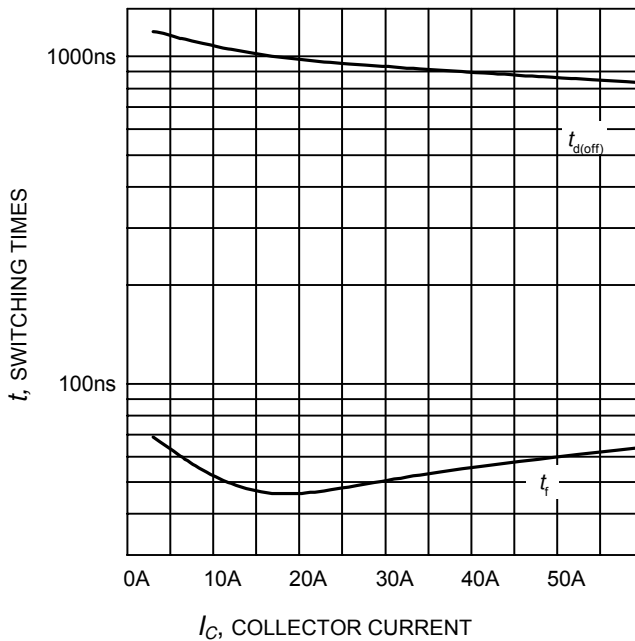
**Figure 6. Typical output characteristic**  
( $T_j = 175^\circ\text{C}$ )



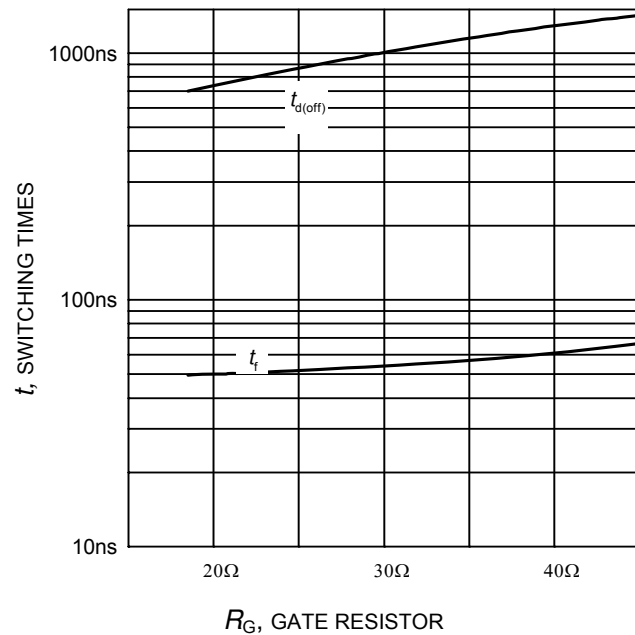
**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )



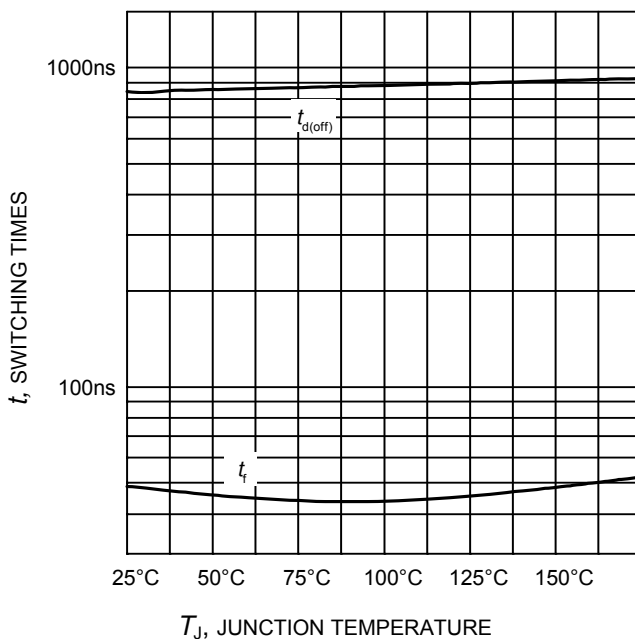
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



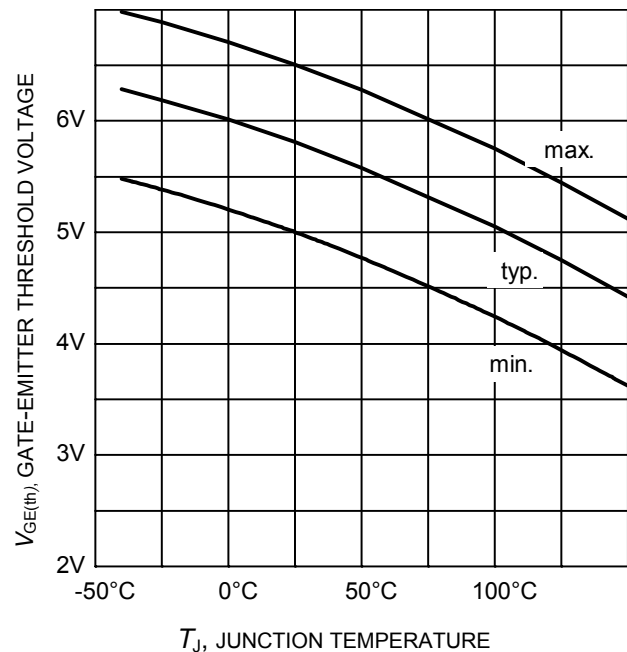
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_J=175^\circ\text{C}$ ,  
 $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $R_G=26.9\Omega$ ,  
 Dynamic test circuit in Figure E)



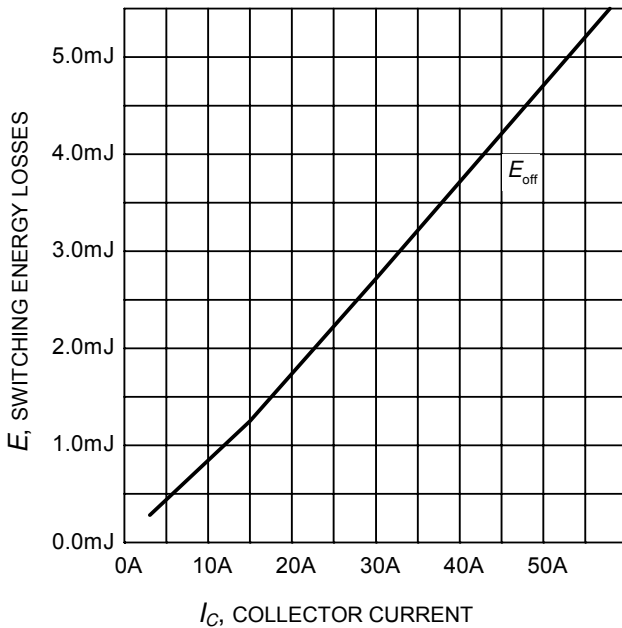
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  
 $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 30\text{A}$ ,  
 Dynamic test circuit in Figure E)



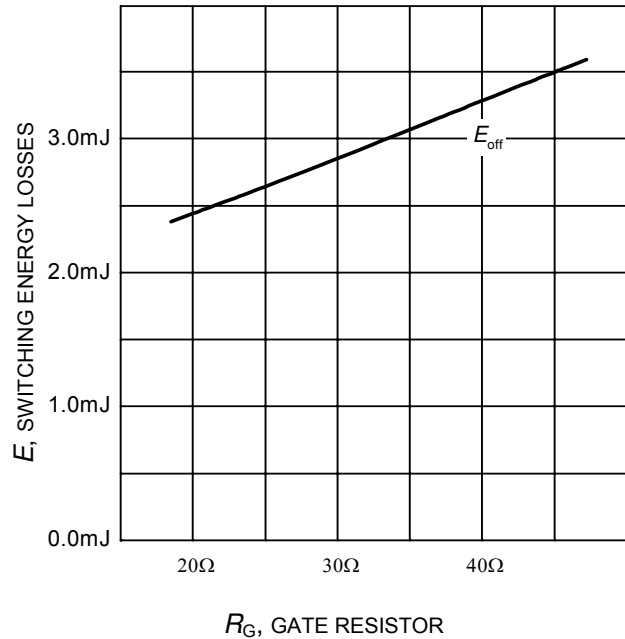
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE} = 600\text{V}$ ,  
 $V_{GE} = 0/15\text{V}$ ,  $I_C = 30\text{A}$ ,  $R_G=26.9\Omega$ ,  
 Dynamic test circuit in Figure E)



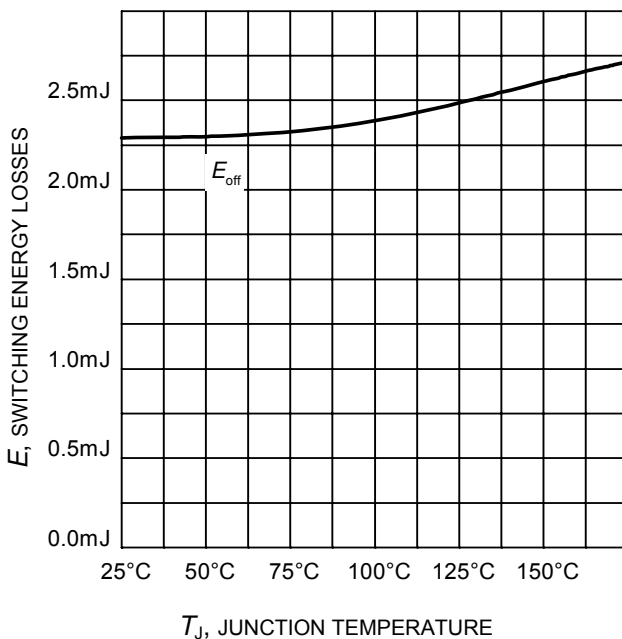
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.7\text{mA}$ )



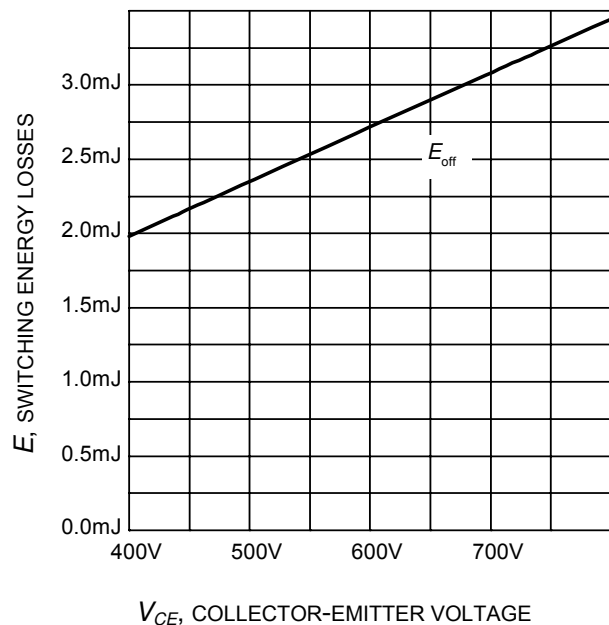
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $R_G = 26.9\Omega$ , Dynamic test circuit in Figure E)



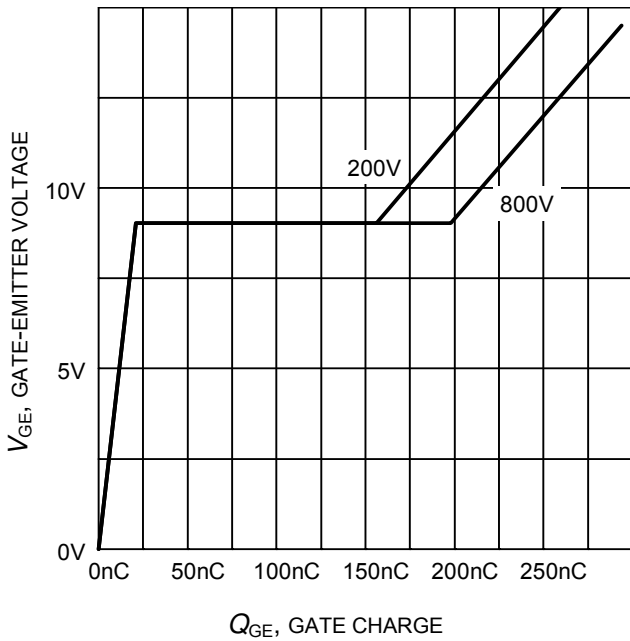
**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 30\text{A}$ , Dynamic test circuit in Figure E)



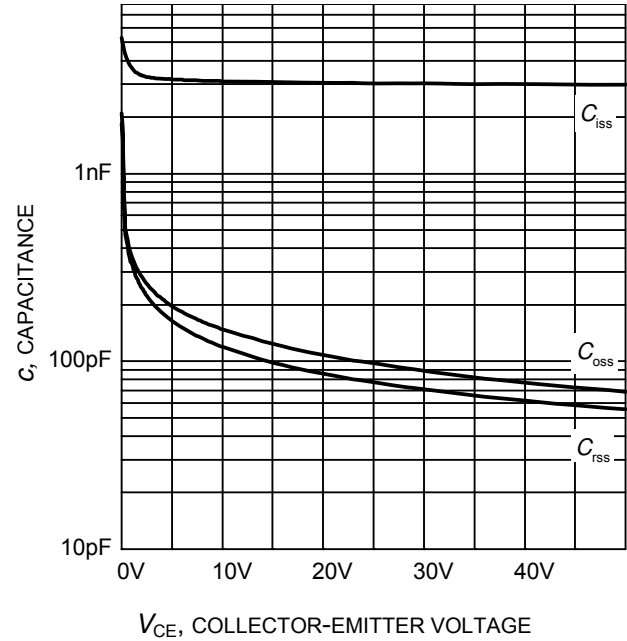
**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 30\text{A}$ ,  $R_G = 26.9\Omega$ , Dynamic test circuit in Figure E)



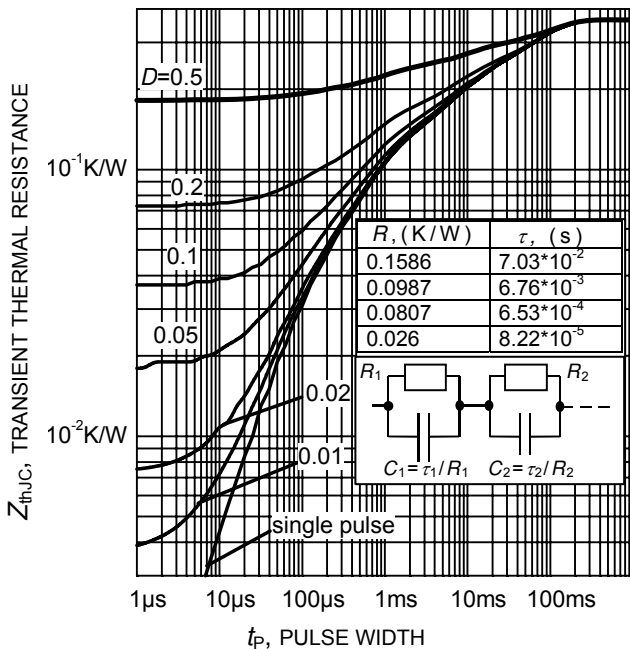
**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 30\text{A}$ ,  $R_G = 26.9\Omega$ , Dynamic test circuit in Figure E)



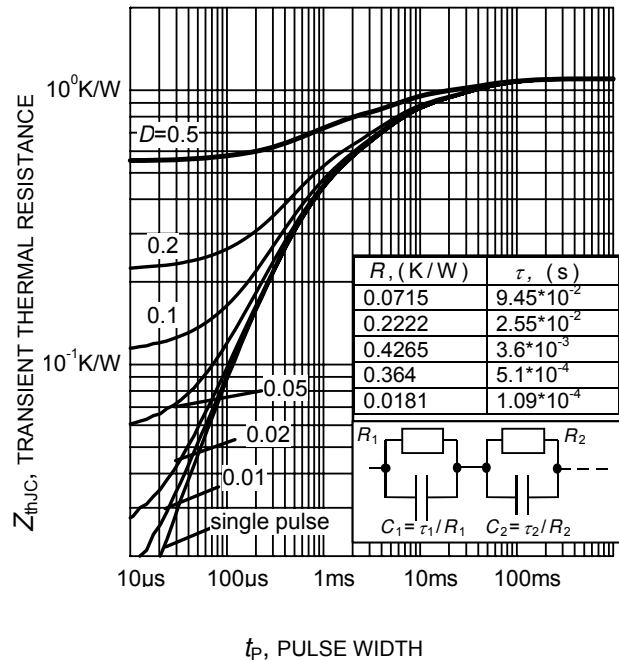
**Figure 17. Typical gate charge**  
( $I_C=30\text{ A}$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f = 1\text{ MHz}$ )

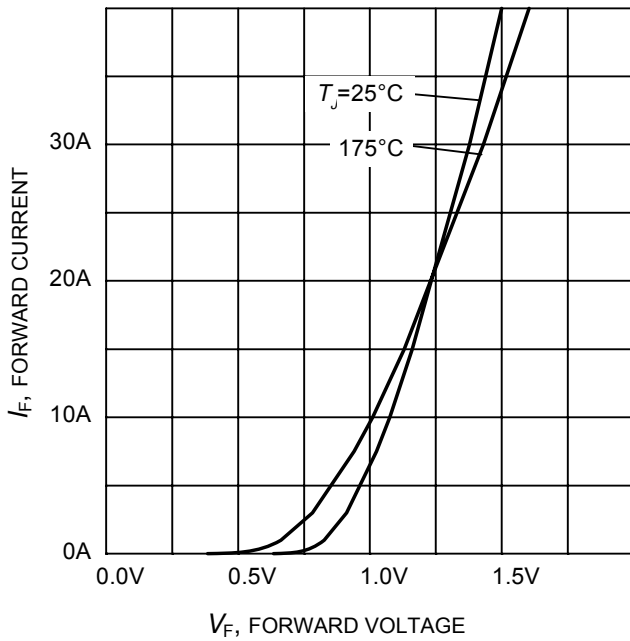


**Figure 19. IGBT transient thermal resistance**  
( $D = t_p / T$ )

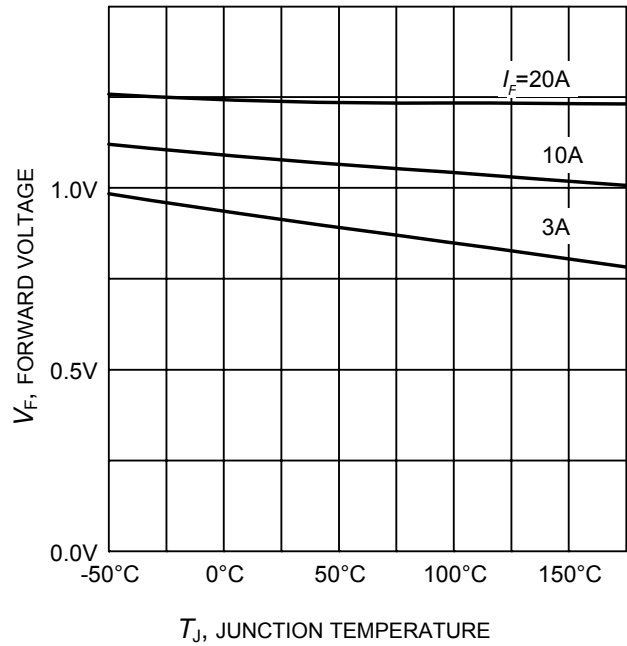


**Figure 20. Diode transient thermal impedance as a function of pulse width**  
( $D=t_p/T$ )



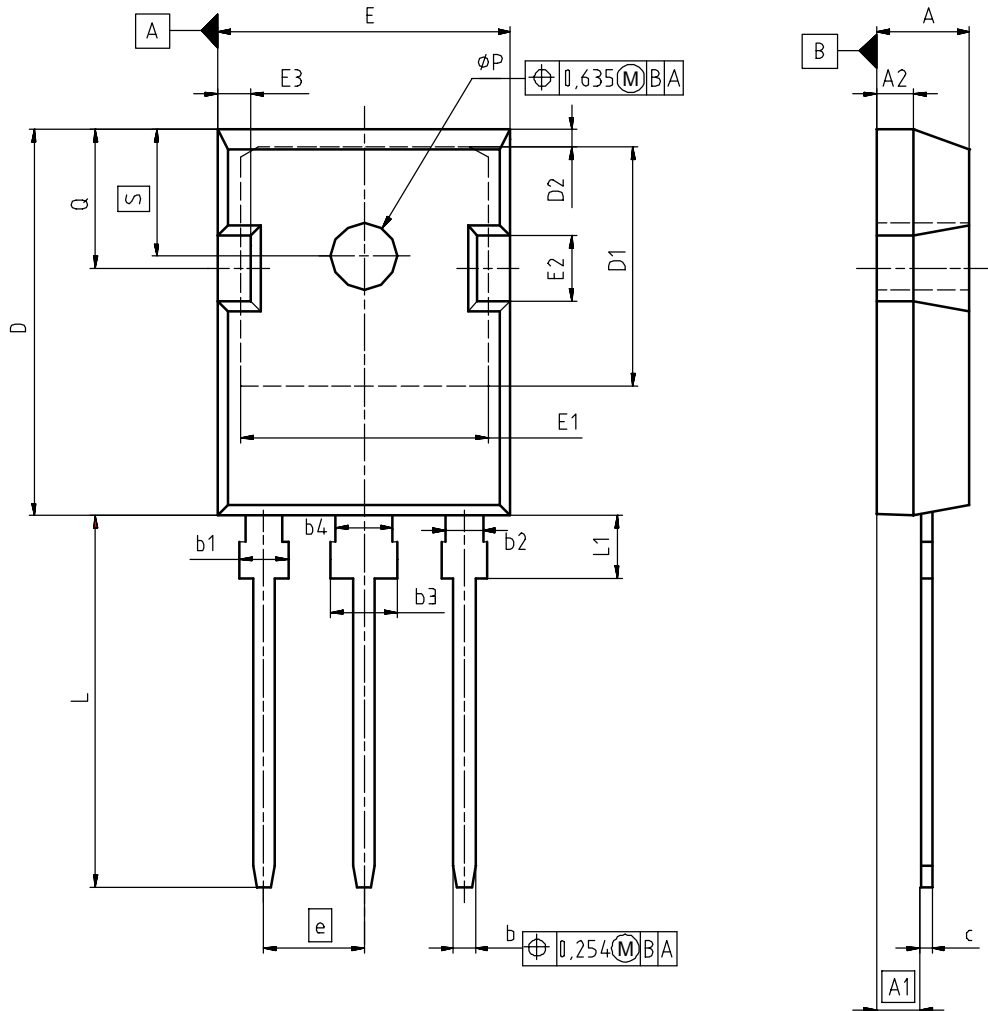


**Figure 21. Typical diode forward current as a function of forward voltage**



**Figure 22. Typical diode forward voltage as a function of junction temperature**

## PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.16	0.193	0.203
A1	2.27	2.53	0.089	0.099
A2	1.85	2.11	0.073	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.82	21.10	0.820	0.831
D1	16.25	17.65	0.640	0.695
D2	1.05	1.35	0.041	0.053
E	15.70	16.03	0.618	0.631
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.68	2.60	0.066	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.31	0.780	0.799
L1	4.17	4.47	0.164	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

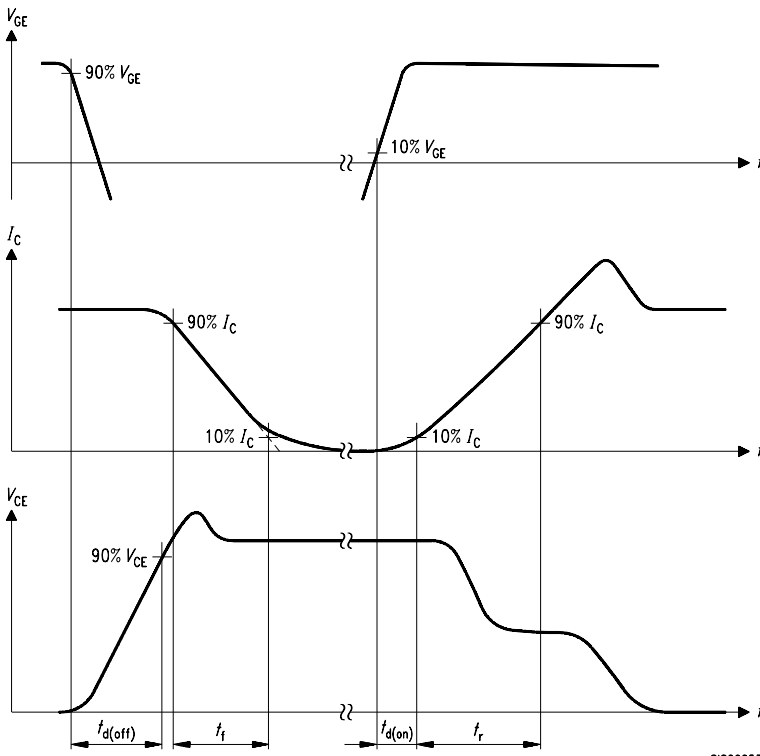
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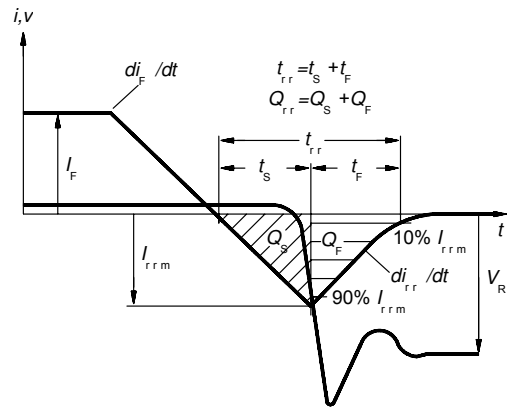
EUROPEAN PROJECTION

ISSUE DATE  
17-12-2007

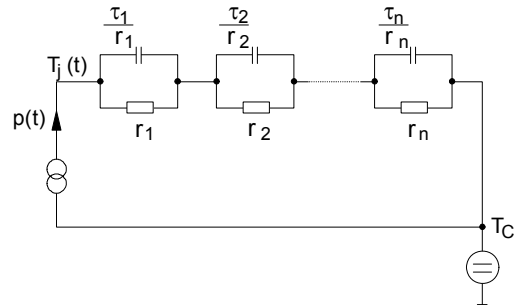
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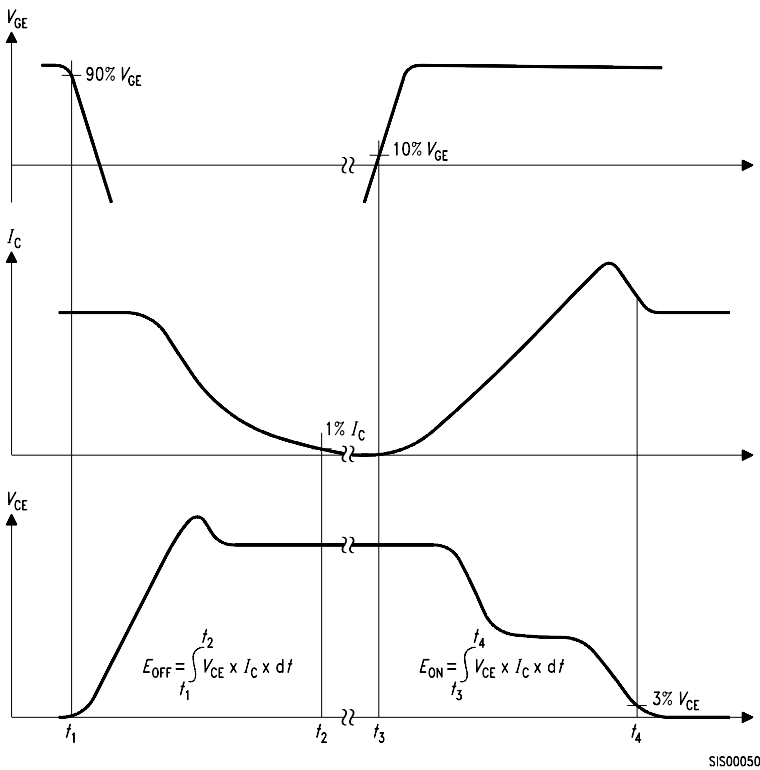
**Figure A. Definition of switching times**



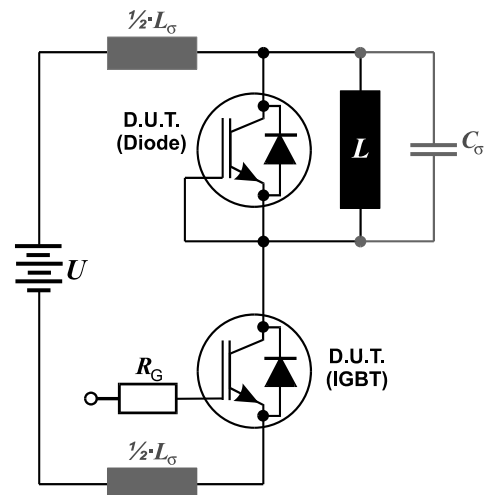
**Figure C. Definition of diodes switching characteristics**



**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**



**Figure E. Dynamic test circuit**

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